Change in the parameters of electron-irradiated 4H-SIC Schottky diodes as a function of the time during low-temperature isothermal annealing
Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; **Toompuu, Jana**; **Sleptsuk, Natalja**; **Rang, Toomas** Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018,Birmingham, UK 2019 / p. 734-737 https://doi.org/10.4028/www.scientific.net/MSF.963.734 Conference proceeding at Scopus Article at Scopus

Dependence of the carrier removal rate in 4H-SIC PN structures on irradiation temperature
Lebedev, Alexander A.; Davydovskaya, Klavdya S.; Kozlovski, Vitali V.; **Korolkov, Oleg**; **Sleptsuk, Natalja**; **Toompuu, Jana** Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018,Birmingham, UK 2019 / p. 730-733 https://doi.org/10.4028/www.scientific.net/MSF.963.730 Conference proceeding at Scopus Article at Scopus

Nano and micro-scale simulations of Si/4H-SiC and Si/3C-SiC NN-heterojunction diodes
Rashid, Muhammad Haroon; **Koel, Ants**; **Rang, Toomas** Silicon Carbide and Related Materials 2018 : 12thEuropean Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018,Birmingham, UK 2019 / p. 357–361 https://doi.org/10.4028/www.scientific.net/MSF.963.357 Conference proceeding at Scopus Article at Scopus